

Pb Free Plating Product

## 2SC2073

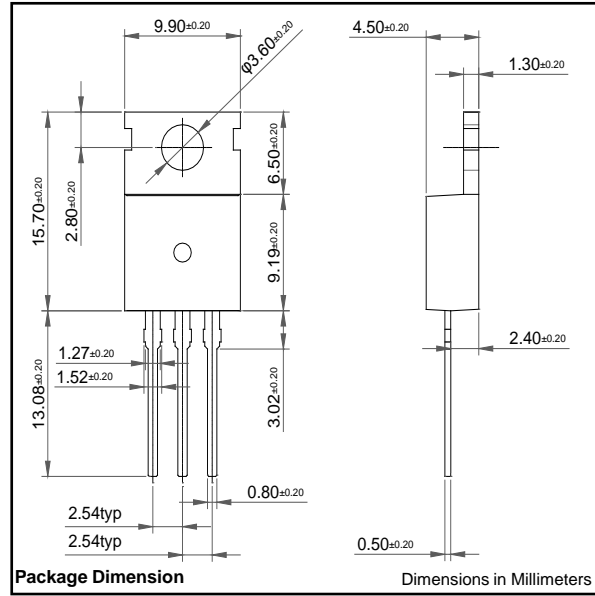


### NPN Silicon Epitaxial Power Transistor

**FEATURES**

- Complements the 2SA940.
- Wide Safe Operating Area.
- Fast Switching Speed.
- Wide ASO.

**TO-220C**  
 1. BASE  
 2. COLLECTOR  
 3. EMITTER



**MAXIMUM RATING** operating temperature range applies unless otherwise specified

Symbol	Parameter	Value	Unit
$V_{CBO}$	Collector-Base Voltage	150	V
$V_{CEO}$	Collector-Emitter Voltage	150	V
$V_{EBO}$	Emitter-Base Voltage	5	V
$I_C$	Collector Current	1.5	A
$I_B$	Base Current	0.5	A
$P_C$	Collector Dissipation	$T_a=25^\circ\text{C}$ $T_c=25^\circ\text{C}$	1.5 25 W
$T_j, T_{stg}$	Junction and Storage Temperature	-55 to +150	$^\circ\text{C}$

## ELECTRICAL CHARACTERISTICS Ratings at 25°C ambient temperature unless otherwise specified.

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base Breakdown Voltage	$V_{(BR)CBO}$	$I_C=100\mu A, I_E=0$	150			V
Collector-emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=1mA, I_B=0$	150			V
Emitter-base Breakdown Voltage	$V_{(BR)EBO}$	$I_E=100\mu A, I_C=0$	5			V
Collector Cut-off Current	$I_{CBO}$	$V_{CB}=120V, I_E=0$			10	$\mu A$
Emitter Cut-off Current	$I_{EBO}$	$V_{EB}=5V, I_C=0$			10	$\mu A$
DC Current Gain	$h_{FE}$	$V_{CE}=10V, I_C=0.5A$	40	75	140	
Collector-emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=0.5A, I_B=50mA$			1.5	V
Base-emitter on Voltage	$V_{BE(on)}$	$V_{CE}=10V, I_C=0.5A$	0.65		0.85	V
Transition Frequency	$f_T$	$V_{CE}=10V, I_C=0.5A$		4		MHz
Collector Output Capacitance	$C_{ob}$	$V_{CB}=10V, I_E=0, f=1MHz$		35		pF

## TYPICAL CHARACTERISTICS @ $T_a=25^\circ C$ unless otherwise specified

